

NON-VOLATILE MEMORY CELL AND MANUFACTURING METHOD THEREOF

Abstract

A non-volatile memory cell includes a substrate, a first isolation structure positioned in a first region on the substrate, a second isolation structure surrounding a second region on the substrate, a control gate positioned on the first isolation structure in the first region, a first insulating layer positioned on the control gate, a second insulating layer positioned on the portion of the substrate in the second region, and a floating gate positioned on the first insulating layer and the second insulating layer.